CIA-RDP86-00513R000515720016-4

2,695 \$/151/61/003/010/022/036 5104/3108

24,7700 (1164,1385,1559)

AUTHORS: Golikova, 0.

Golikova, O. A., Moyznee F. Yv. and Still lans, L. S.

TITLE:

Hole mobility in germanian as a function of concentration and temperature

PERIODICAL: Fizika tverdogo tela v. 5. ni. 6, 1961. 6105 - 3114

TEXT: The hole mobility in p-type germanium with an acceptor concentration of  $4.9\cdot10^{13}$  -  $4\cdot10^{20}$  cm<sup>-2</sup> was investigated in the temperature range of from 77 to  $450^{\circ}$  K. The carrier concentration was determined by measuring the Hall effect in magnetic fields of  $50 \cdot 18,000$  ce in the above range of temperatures. Specimens were produced by zone melting during which the germanium was alloyed rith galloun. Mobilities of different specimens as functions of temperature are given in Figs. 1 and 2.

The carrier concentrations of the different aperimens ranged from  $4.9 \cdot 10^{13}$  to  $6.4 \cdot 10^{16}$  cm<sup>-3</sup> at  $77^{\circ}$ K (Fig. 1), and from 1.28 C  $^{\circ}$  to  $4.2 \cdot 10^{20}$  cm<sup>-3</sup> at  $300^{\circ}$ K (Fig. 2). The measurement results were checked with specimens

Card 1/5

Hole mobility in germanium. . Broadcad at the Institut metallurgii AN SSSR (Institute of Notalling), produced at the Institut metallurgii AN SSSR (Institute of Notalling), AS USSR) by Chosmani'skiy's method. Results are given in Fig. 4. In a letailed discussion of the results the authors show that in the range of carrier modifity in p-type germanium in the temperature range from 77 to 250 K can be explained qualitatively and quantitatively by theories of carrier scattering from ionized impurities. The modility is one-hundredth of that of pure materials. The ratio u theory explained of hearty of at 10 metric of concentrations of 10 metric of explaining from a concentration of 50 metric of metric of the state of

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Hole mobility in mermanium .

R. K. Willardson. Phys. Rev., 110, 126, 126.

ASSOCIATION: Institut poluprovodnika: All SSSR Leninared (Institute of Semiconductors AS USER, Leningred)

SUBMITTED: May 27, 1961

Fig. 1. Hall mobility as a function of temperatures legend: The figures by the curves indicate the number of specimen. On top-specimens with lower carrier concentration.

Fig. 2. Hall mobility as a function of temperature. Legend: see Fig. 1.

Fig. 3. Hall mobility as a function of earnier concentration at room temperature. Legend: (1) specimen examined in the greent paper; (2) specimens supplied by the Institute of Metallarsy. AS USSE; (3) data taken from the paper of F. A. Trumbere et al.; (4) data taken from the paper of W. C. Dunlap, Phys. Rev., 70, Lot. 1951.

Card 3/5 )

29696 \$/181/61/003/010/023/036 B125/B102

24,7600 (1043,1137,1164)

Card 1/3

AUTHORS: Golikova, O. A., and Stillbans, L. S.

TITLE: Investigation of the dependence of the Hall coefficient on

the magnetic field and the temperature in p-type germanium

PERIODICAL: Fizika tverdogo tela, v. 5, ac 10, 1961, 3115-3122

TEXT: The authors study the function R(H) (R-Hall coefficient) for carrier concentrations of  $n\sim 10^{-13}$  to  $10^{-16}$  cm  $^{-3}$  at magnetic field strengths of 50 to 38,000 oe, and at temperatures of  $77-290^{\circ}\mathrm{K}$ . The experimental results are compared with theory (A. C. Beer, R. K. Williardson, Phys. Rev., 110, No. 6, 1286,1953). The experimental results obtained for samples with  $n\sim 10^{-13}$  to  $10^{-14}$  are in semiquantitative agreement with theory. Agreement is found at mobilities lower than the theoretical values. According to G. Dresselhaus, A. F. Kip. and C. Kittel (Phys. Rev., 98, no. 2, 398, 1955) (Determination of the relaxation times  $\tau_1$  and  $\tau_h$  of light and heavy holes, respectively, from the width of the

29696 5/181/61/003/010/023/036 B125/B102

Investigation of the dependence of.

resonance curve at  $4^{\circ}$ K), the following relation is valid:  $\tau_1/\tau_n \simeq 1.4$  and not  $\tau_1/\tau_h=1$ . The results concerning galvanomagnetic effects were in conformity with theory at b =  $m_h/m_1$  = 8 ( $m_h$  and  $m_i$  are the effective masses of heavy and light holes, respectively)  $v = n_1/n_n = 0.02$  was put instead of  $\nu = 0.04$ . ( $n_1$  and  $n_h$  are the concentrations of light and heavy holes, respectively). According to J. Ye Pikus (ZhETF, XXVII, no. 7, 1957), taking account of the angular dependence may lead to a difference between  $\tau_1$  and  $\tau_h$ ; hence, the value b = 8 used for the calculations appears to be doubtful. The values of b obtained for various scattering mechanisms (consideration of a possible influence of optical vibrations and of hole-hole scattering) should be taken into account in a more exact theory. M. N. Vinogradov is thanked for aid in measurements, E. S. Shalyt for arranging measurements of the Hall effect in strong magnetic fields, I. I. Farbsteyn for advice, as well as G. L. Bir, B. Ya. Moyzhes, and G. Ye. Pikus for discussions. There are 6 figures, 2 tables, and 12 references: 4 Soviet and B non-Soviet The three most recent

Card 2/3

23696 S/181/61/003/010/023/036 B125/B102

X

Investigation of the dependence of.

references to English-language publications read as follows:

R. K. Willardson, T. C. Harman, A. C. Beer, Phys. Rev., <u>76</u>, 1512, 1954;

H. Brooks. Advances in Electronics, <u>7</u>, 156, 1955; F. J. Morin, Phys. Rev., <u>93</u>, no. 1, 62, 1954.

ASSOCIATION: Institut poluprovodníkov AN SSSR Leningrad (Institute of

Semiconductors AS USSR, Leningrad)

SUBMITTED: May 27, 1961

Card 3/3

44.171

5/181/62/004/012/019/052 B104/B102

AUTHORS:

Golikova, O. A., Moyzhes, B. Ya., and Orlov, A. G.

TITLE:

The mobility of holes in germanium as a function of their

concentration and temperature

PERIODICAL:

Fizika tverdogo tela, v. 4, no. 12, 1962, 3482-3491

TEXT: A previous work (C. A. Galikova et al., FTT, 3, 10, 1961) in which the carrier mobility of gallium-doped p-type germaniun was determined between 77 and 450°K is here continued. Ge specimens having gallium concentrations of up to 7.10°C cm<sup>-3</sup> were used for determining the electrical conductivity and the Hall effect between 450 and 1000°K, at which temperatures a noticeable electron concentration already arises. In calculating the carrier mobility, the collisions between carriers for a nondegenerate electron gas and the scattering from both accustic and optical vibrations were taken into account. This permitted of comparing theory with experiment at higher temperatures also. The measurements were made in an argon atmosphere using platinum probes and Pt-PtRh thermocouples. It was possible to determine the temperature dependence of the Hall effect at Card 1/2 (1.5/161/6)/063/010/072/174

s/181/62/004/012/019/052 B104/B102

The mobility of holes in germanium ...

magnetic field strengths up to 10 koe. Results: At temperatures below 300°K, the experimental and theoretical results agree fairly well if the scattering from optical and acoustic vibrations, from ionized and neutral impurities and the scattering of holes from holes is taken into account. At higher temperatures the theory differs considerably from experiment, which is explained by the fact that the mobility in scattering from lattice vibrations decreases more rapidly than is predicted by theory:

 $u_{\rm lattice} \sim T^{-5}$  instead of  $T^{-2.5}$ . This strong decrease cannot be explained by the fact that the carrier energy approaches the spin-orbital splitting in germanium ( $\Delta$  = 0.29 eV). Spectral analyses showed that with

 $n < 5 \cdot 10^{19}$  cm<sup>-3</sup> at nitrogen temperature the Hall concentration equals that of the gallium atoms; in the case of stronger alloying, the concentration determined from Hall coefficient is too high. There are 9 figures and 2 tables.

ASSOCIATION:

Institut poluprovodnikov AN SSSR, Leningrad (Institute of

Semiconductors AS USSR, Leningrad)

SUBMITTED:

July 6, 1962

Card 2/2

L 18001-63 EWP(g)/EWT(m)/BDS: AFFEC/ASE ... JO/JO 5/0181/63/005/006/1657/1667 ACCESSION MR: AP3001287 AUTHORS: Vinogradova, M. N.; Golikova, O. A.; Dubrovskaya, I. N.; Moyzhes, B. Ya. TITLE: Thermoelectromotive force of p-type germanium in relation to concentration and temperature SOURCE: Fizika tverdogo tela, v. 5, no. 6, 1963, 1657-1667 TOPIC TAGS: thermoelectromotive force, Ge, Ga, intrinsic conductivity, Hall effect, current carriers, Chromel, Copel, p-type semiconductor ABSTRACT: The authors undertook this study because of lack of data on either polycrystalline material or single crystals naving high concentrations of current carriers. They investigated single crystals in the concentration interval  $7 \times 10^{17}$  to  $7 \times 10^{20}$  per cm<sup>3</sup> and the temperature interval 300-950K. Specimens were prepared by zone refining, during which the Ge was alloyed with Gam Concentration of current carriers was determined by measuring the Hall effect. To avoid errors resulting from surface attachment of thermocouples, the thermoelectromotive force was measured by thermocouples of Chromel-Copel welded to platinum pins driven into small holes (0.3 mm) in the specimens. Measurements at high temperatures were made in an argon atmosphere. Variations between computed and Card 1/2,

#### "APPROVED FOR RELEASE: 09/24/2001

CIA-RDP86-00513R000515720016-4

L 18001-63

ACCESSION NR: AP3001287

experimental values were observed for concentrations above  $10^{20}~\mathrm{per}~\mathrm{cm}^3$  at 300K and also for lower concentrations at temperatures above 300K. These have been explained by deviations from the square law of dispersion with increase of energy. This explanation is in agreement with the change of electrical conductivity, the Hall constant, and the thermoelectromotive force in the region of almost intrinsic conductivity. "The authors thank L. S. Stil'bans for his interest in the work, A. V. Ioffe for making the measurements on thermal conductivity, and A. V. Petrov for advice on the technique of measuring the thermo-electromotive force. Orig. art. has: 7 figures, 1 table, and 16 formulas.

ASSOCIATION: Institut poluprovodnikov AN SSSR, Leningrad (Institute of Semiconductors, Academy of Sciences, SSSR)

SUBMITTED: 24Dec62

DATE ACQ: 01Jul63

ENCL: 00

SUB CODE: PH

NO REF SOV: 007

OTHER: 015

JD EWP(q)/EWT(m)/BDS AFFTC/ASD

s/0181/63/005/006/1753/1755 L 18043-63

ACCESSION NR: AP3001309

AUTHOR: Golikova, O. A.

TITLE: Mobility of electrons in Ge at temperatures above room temperature

SOURCE: Fizika tverdogo tela, v. 5, no. 6, 1963, 1753-1755

TOPIC TAGS: electron, mobility, Ge, Sb, alloy, scattering, vibration,

temperature, lattice

ABSTRACT: The author undertook this study because of inadequate information on such mobility at higher temperatures. In computin; the dependence of mobility on temperature, values at room temperature coincided with experimental values with an accuracy of 20-40%. This precision is considered satesfactory in light of the great con ribution of ions in scattering and in view of the approximate nature of the existing theory on scattering by ion:. At higher temperatures this contribution should lessen and the agreement with experimental data should improve, but if mobility with scattering at thermal vibrations is taken into account, the reverse is found: at higher temperatures the computed values diverge more and more from experimental values. By considering mobility during scattering at

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ACCESSION NR: AP3001309

lattice vibrations (at temperatures above 290K) coincidence between calculated and experimental results was obtained within an accuracy of 20%. It was found that 1.f the mobility in a sample at room temperature is 35% lower than for such a sample containing Sb, at high temperatures the mobilities of the two are within 10-15% of each other. It may be assumed that the dependence of electron mobility (during scattering at thermal vibrations) is practically unaffected by the kind of alloying material. "The author thanks V. S. Zemskov and A. D. Beluya for furnishing samples and B. Ya, Moyzhes and L. S. Stil'bans for their interest in the work." Orig. art. has: 1 figure.

ASSOCIATION: Institut poluprovodnikov AN SSSR, Leningrad (Institute of Semi-

conductors, Academy of Sciences, SSSR)

SUBMITTED: 16Feb63

DATE ACQ: 01Jul63

ENCL: 00

SUB CODE: PH

NO REF SOV: 004

OTHER: 003

Card 2/2

## "APPROVED FOR RELEASE: 09/24/2001

CIA-RDP86-00513R000515720016-4

AFFTC/AFD/ESD-3/ EWT(1)/EWG(k)/EWP(q)/EWT(m)/BDS/EEC(b)-2 L 17109-63 JD/AT IJP(C) Pz-4

\$/0181/63/005/007/1908/1912

AF3C03E87 ACCESSION NR:

AUTHORS: Golikova, O. A.; Orlov, A. G.

TITLE: Mobility of holes in Go alloyed with Al and In 27

5, no. 7, 1963, 1908-1912 SOURCE: Fizika tverdogo tela,

TOFIC TAGS: mobility, hole, Ge, Al, In, alloy, spectral analysis, Hell coefficient, magnetic field, Hell emf, impurity atom, local distortion

ABSTRACT: This is a continuation of previous work on Ge allowed with Gn by O. A. Golikova, B. Ya. Loyzhes, and A. G. Orlov (FTT, 4, 3482, 1962). In the present study the Hall coefficient was measured in a regnetic field of 20 COO cersteds, permitting the authors to obtain measured values of Hall end at the highest concen-trations (greater than 1020 cm-3) on the order of several tens of my in a sample about 1 mm thick and with currents of 1-2 cmp through the sample. Measurements were made in the temperature range 77-300K. The mobilities of holes in samples alloyed with Al, throughout the entire temperature renge end at concentrations from 1017 to 1021 cm-3, agree with mobilities obtained previously on samples alloyed with Ga, within 10% or less (values on Go olloy taken from paper cited above). robilities of holes in samples alloyed with In proved to be less than in samples Card 1/2

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ACCESSION NR: AP3003887

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alloyed with Ga and Al. At concentrations greater than 1020 cm<sup>-3</sup> the Hall concentration was observed to exceed the Al concentration as determined by spectral analysis. "The authors thank V. S. Zemskov and A. D. Belaya for furnishing samples and B. Ya. Novehes and L. S. Stillbans for interest in the work and for valuable counsel." Orig. art. has: 2 figures and 1 table.

ASSOCIATION: Institut poluprovednikov AN SSSR, Leningred (Institute of Semiconductors, Academy of Sciences, SSSR)

SUBLITTED: 16Feb63

DATE ACQ: 15Aug63

BICL: 00

SUB CODE: PH

NO REF SOV: COS

OTHER: 008

Card 2/2

L 19628-65 EWT(m)/EWP(t)/EWP(b) AFWL/SSD/ASD(m)-5/ESD(gs)/IJP(c) JD
ACCESSION NR: AP4041738 S/0181/64/0D6/007/2202/2204

AUTHOR: Golikova, O. A.

TITLE: Effective mass of holes in degenerate german um

SOURCE: Fizika tverdogo tela, v. 6, no. 7, 1964, 2202-2204

TOPIC TAGS: hole conduction, carrier mobility, germanium, carrier density, carrier effective mass

ABSTRACT: In order to check on the conclusions of earlier results by the author (O. A. Golikova, B. Ya. Moyzhes, A. S. Stillbans, FTT v. 3, 3105, 1961; O. A. Golikova, B. Ya Moyzhes, A. G. Orlov, FTT, v. 4, 3483, 1962; O. A. Golikova, A. G. Orlov, FTT, v. 5, 1908, 1963) that the mobility of the holes in germanium decreases at 77-2300K much more rapidly than would follow from the theory in the casa of strong degeneracy and scattering by impurity ions and lattice vibrations, the author calculated the effective mass of the holes as

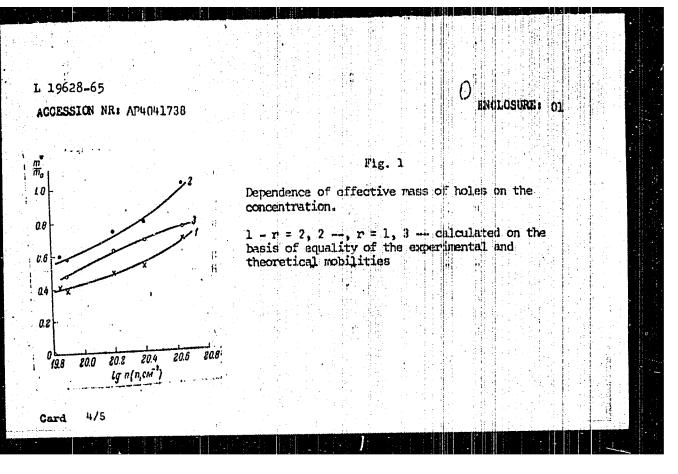
Card 1/5

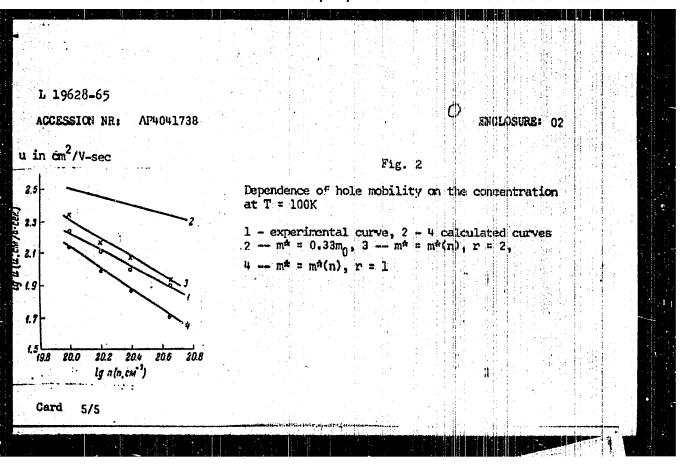
L 19628-65

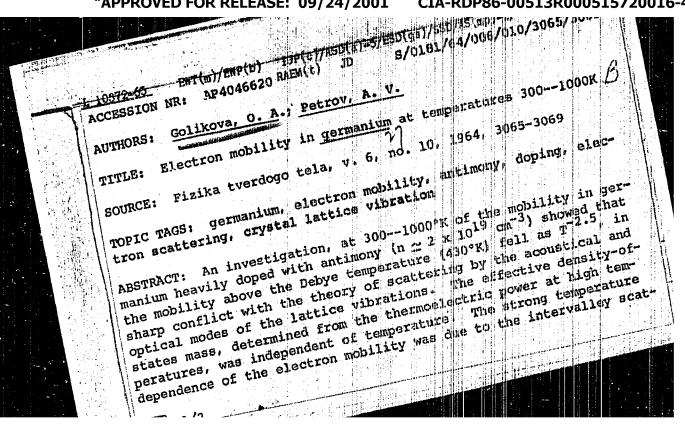
ACCESSION NR: AP4041738

a function of their density obtained from data on the rmal enf of very strongly doped germanium specimens (n > 1020 cm 3). Such calculations are also of interest because there are still no published data on the effective mass of holes in strongly degenerate p-germanium specimens. It is shown that in the case of very high concentration the predominant contribution to the scattering is made by the impurity ions. The effective mass is found to increase with condentration and to be dependent on the scattering parameter. The values of the mobility calculated at a constant effective mass (m\* = = 0.33  $m_0$ , where  $m_0$  -- mass of free electron) exceed the experimental values by 2--3 times. On the other hand, if the concentration dependence of m\* is taken into account, the values agree within 15--30% if r = 2. For r = 1 the agreement is poorer, but there are grounds for assuming that 1 < r < 2. It is concluded that, in view of the correlation between the results for the mobility and the thermal emf, the concentration dependence of the mobility can be regarded as governed by the growth of the effective mass of the holes with in-Card 2/5

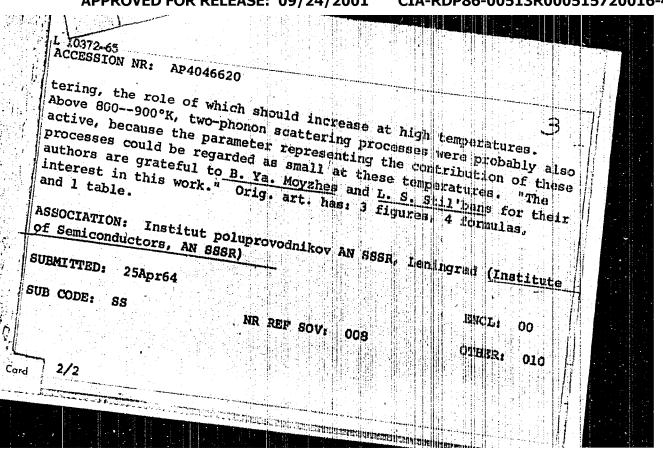
L 19628-65 ACCESSION NR: AP4041738				
creasing concentration (quantitatively. Orig. as	energy), not	only qualitati	velly but also	
	oluprovodniko		ingrad [Institut	
SUBMITTED: 24Feb64			enci: 02	
SUB CODE: SS, EC	NR REF SO	DV: 004	OTHER: 003	
Card 3/5				







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	·	(e)/EWT(m)/EWP(t)/EWP() SOUR	CE CODE: UR/O	81/65/002/000/0	1000/0000
AUTHOR:	Golikova, O.	Avgustinnik, A. I.	; Klimashin, G.	M + You launt t	60
		conductors AN SSSR (Intitute im. Lensovet		vodnikov AN SSS khnologicheskiv	R); Lenin-
TITLE:	Electrical prop	perties of titanium car	hide	g. =oun.zy	zim erede)
SOURCE:	Fizika tumndan	19 =	7		
	gr. 47	o tela, v. 7, no. 9, 1	965, 2860-2862		
TOPIC TA	IGS: electric n	roperty, titanium compo ce, Fermi level	ound, carbide,	energy band str	ructure,
resistiv of TiC <sub>x</sub> mens. Co of temper defect co	ity, thermoelect (x = 0.43-1.0). urves are given- rature in the 30	study the electrical properties. The data are used to the control of the control	scattering of all constant were thods were used dermoelectromotrious values of	current carrier e measured in s for producing ive force as fur	s. The pecimens the speci-
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L 9244-66 ACC NR: AP5022743 in concentration. It is assumed that the Ti-C bond is basic in stoichiometric TiC and that the Ti-Ti bond is strongly screened. The Ti-Ti bond becomes more and more important as the carbon content in the compound is increased. The stronger this bond becomes, the wider the conduction band and the greater the deviation from semiconductor properties. The rapid increase in thermoelectromotive force at high temperatures is explained by assuming that the "metal" conduction band overlaps the higher conduction band of stoichiometric titanium carbide. At high temperatures, the Fermi level falls into the higher band and thermoelectromotive force begins to increase more rapidly. This hypothesis is confirmed by  $\alpha(T)$  curves. Orig. art. has: 2 figures, 1 table. SUB CODE: 20/ SUBM DATE: 14Apr65/ ORIG REF: 003/ OTH REF: 002

L 15736-66 EWT(1)

ACC NR: AP6000898 SOURCE CODE: UR/0181/65/007/012/3698/3700

AUTHORS: Golikova, O. A.; Avgustinnik, A. I.; Klimashin, G. M.; Kozlovskiy, L. V.; Ordan'yan, S. S.; Snetkova, V. A.

ORG: Institute of Semiconductors, AN SSSR, Leningrad (Institut poluprovodnikov AN SSSR)

TITLE: Electric properties of <u>carbides</u> of the <u>transition metals</u> of group IV

SOURCE: Fizika tverdogo tela, v. 7, no. 12, 1965, 3698-3700

TOPIC TAGS: titanium compound, zirconium carbide, hafnium compound, carbide, thermal emf, Hall constant, resistivity, transition element

ABSTRACT: The purpose of the investigation was to compare the electric properties (thermal emf, resistivity, Hall constant) of TiC, ZrC, HfC as functions of the composition in the temperature interval 300 -- 1500K. The data on TiC were taken from an earlier investigation by the authors (FTT v. 7, 2860, 1965). The ZrC and HfC were prepared by the same technology as the TiC. The plots of all the measured

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ACC NR: AP6000898

quantities against the carbon concentration are approximately the same for all three carbides. This demonstrates that the scattering mechanism and energy spectrum of the carriers are the same in all the compounds. An unexpected result is the fact that the effective masses of the three carbides are qual, since their lattices have different lattice constants and the participating electrons come from different shells. From the fact that the ratio of the distances between the metal and carbide atoms (R) and the radii of the metallic atoms (r) is also constant for all carbides, it is concluded that the orbitals of the metal atoms overlap equally. This explains the equality of the effective masses. The carrier scattering mechanism is briefly discussed. Orig. art. has: 2 figures, 1 formula, and 1 table.

SUB CODE: 07 / SUBM DATE: 23Ju165/ ORIG REF: 004/ OTH REF: 003/

Card 2/2

ACC NR: AP6006837 SOURCE CODE: UR/0181/66/008/002/0500/0506.

AUTHOR: Golikova. O. A.; Iordanishvili, Ye. K.; Petrov, A. V.

ORG: Institute of Semiconductors, AN SSSR, Leningrad (Institut poluprovodnikov AN SSSR)

TITLE: Electrical properties of solid solutions in the Si-Ge system

TOPIC TAGS: solid solution, germanium, silicon, current carrier, conduction band, semiconductor band structure . electric property

SOURCE: Fizika tverdogo tela, v. 8, no. 2, 1966, 500-506

ABSTRACT: Experimental data are given on the electrical properties of heavily doped specimens of solid solutions containing 5-30 at % Ge in p-silicon and 15-30 at % Ge in n-silicon at temperatures from 100 to 1100°K with particular regard to the mechanism responsible for scattering of current carriers by lattice vibrations at high temperatures (above 400°K), by ion impurities for the case of deep alloying and by nonhomogeneities in the solid solution. The authors discuss data on the energy spectrum of holes and electrons at high energies produced by two independent

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L 23154-66

ACC NR: AP6006837

methods: increasing the temperature and filling the bands (deep alloying). Curves are given for thermoelectromotive force as a function of current carrier concentration in silicon-germanium solid solutions of both conductivity types. Graphs are also given showing hole and electron mobility as functions of carrier concentration for various solid solutions. The resultant data are used for calculating the effective mass of the density of electron states. It is found that the effective mass for the density of states in solid solutions of germanium in silicon is comparable to that observed in pure silicon and increases with temperature. This indicates that the parameters of the conduction band in solid solutions with a composition close to that of silicon remain the same as in pure silicon. From this, it may be concluded that the amplification effect in Si-Ge solid solutions is extremely small. We are sincerely grateful to V. S. Zemskiy, V. V. Rozhdestvenskaya and R. S. Yerofeyev for furnishing the specimens and to B. Ya. Moyzhes for participating in discussion of the work. Orig. art. has: 5 figures, 3 formulas.

SUB CODE: 20/

SUBM DATE: 16Apr65/

ORIG REF: 005/

OTH REF: 015

Card 2/2

I. 000/5-61 LOS (47/06/2(47/45 U(5)/ETE 140(6) AT/AB/45 UL/AB ACC NR: AT6027151 SOURCE CODE: UR/0000/65/000/000/0241/0244

AUTHOR: Avgustinik, A. I.; Golikova, O. A.; Klimashin, G. M.; Kozlovskiy, L. V.; Keshpor, V. S.

ORG: none

TITLE: Dependence of certain electrophysical properties of titanium monocarbide on the carbon content

SOURCE: AN SSSR. Otdeleniyo obshchey i tekhnicheskoy khimii. Issledovaniya v oblasti khimii silikatov i okislov (Studies in the field of chemistry of silicates and oxides). Moscow, Izd-vo Nauka, 1965, 241-244

TOPIC TAGS: titanium compound, carbide, Hall constant, Hall mobility, conduction electron, resistivity, carbon

ABSTRACT: The dependence of the resistivity  $\rho$ , thermal emf  $\omega$  and Hall constant R of titanium monocarbides on the carbon content was studied in the region of homogeneity on samples prepared from powdered Ti and acetylene black at 1750°. All the samples showed a negative Hall constant, indicating an n-type conductivity; the absolute value of R decreases rapidly with decreasing carbon content, indicating an increase in the concentration of free conduction electrons. The absolute differential thermal emf also decreases with diminishing carbon content. The resistivity decreases with decreasing carbon content in monocarbide phases TiCx, this being in accord with the in-

Card 1/2

L 06296-67 EWT(m)/EWP(a)/EWP(t)/ETI IJP(z)AT/WH/JD/JG/GD ACC NRI AT6027152 SOURCE CODE: UR/0000/65/000/000/02/44/0250 (A)AUTHOR: Avgustirik, A. I.; Golikova, O. A.; Klimashin, G. M.; Kozlovskiy, L. V. CRG: none TITIE: Effect of oxygen on certain properties of titanium carbide SOURCE: AN SSSR. Ctdeleniye obshchey i tekhnicheskoy khimii. Issledovaniya v oblasti khimii silikatov i okislov (Studies in the field of chemistry of silicates and oxides). Moscow, Izd-vo Nauka, 1965, 214-250 TOPIC TAGS: titanium compound, carbide, oxygen impurity ABSTRACT: In a study of alloys of the TiC-TiC-Ti system, x-ray structural data showed that the contamination of TiC, with oxygen causes a decrease in the size of the unit cell, this effect being more pronounced the closer the composition is to the steichio metric proportion of  $\mathrm{TiC}_{\mathrm{X}}$ . This along with the influence of vacancies accounts for the great scatter of results obtained by various authors in their study of the lattice parameter of TiC1.0. The melting point and microhardness of titanium carbide centarinated with oxygen decrease with increasing number of defects in the lattice, and to a lessor degree depend on the kind of metalloid atoms. As the oxygen content rises, the microbrittleness decreases at first, then begins to increase because of increasing ionic bond character. The electron concentration in titraium carbide containing some oxygen is influenced by two effects; when the number of vacancies in the metalloid Card 1/2

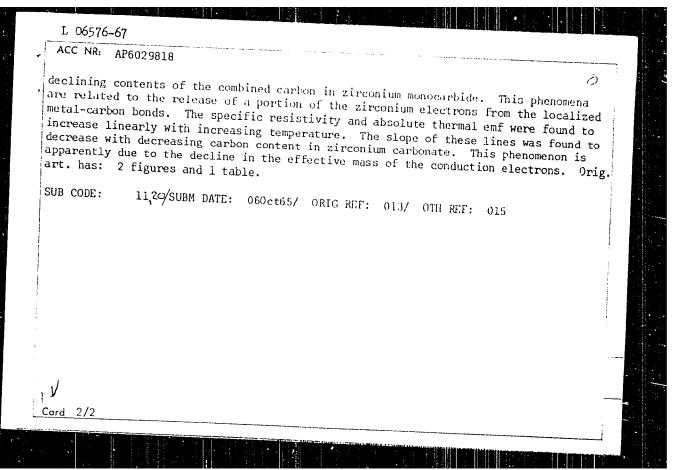
L 06296-67 ACC NR: AT6027152

sublattice (i. e., the number of conduction electrons) is small, the current carrier concentration grows, since oxygen atoms give up to the conduction band their excess electrons relative to carbon. When the number of vacancies in the metalloid sublattice is large, the oxygen atoms do not give up their electrons, and oxygen in its reaction with titanium ties up the titanium electrons, causing a drop in the carrier concentration. Titanium carbide containing an oxygen admixture shows a metallic tomperature dependence of the resistivity and thermal omf. The mobility of electrons at T = const drops with their increasing concentration and is relatively insensitive to the concentration of defects in the metalloid sublattice. The predominant scattering mechanism appears to involve scattering by lattice vibrations, and the energy dependence of the relaxation time is close to that observed in semiconductors. Orig. art.

SUB CODE: 07/ SUBM DATE: 09Apr65/ ORIG REF: 009/ OTH REF: 003

Card 2/2 16-

L 06576-67 E.T(m)/E.T ACC NA: AP6029818 (	(a)/mm(w), hin (t)/mmi	(a) AD AM AD AD UR/0363/66/002/008/1439	/1443 55
AUTHOR: Avgustinik, A. Ordan'yan, S. S.; Snetko	I.; Golikova, C. A.; Klimas va, V. A.	hin, G. M.; Neshpor, V. S.	
institut); Seniconductor peluprevodnikov Ako TITLE: Dependence of ce monocarbide on the carbo	e of Technology im. Lensove  - Twstilote, Newberny of S  Advisor New SSSR)  rtain electro- and thermoph  n content within the range  iya. Neorganicheskiye mater	ysical properties of zirco of homogeneity	nium
TOPIC TAGS: zirconium of electric conductivity, to ABSTRACT: The dependence ficient, and thermal concentration of contents in the carbic purity zirconium and car properties, compositions graphed and tabulated.	arbide, solid mechanical prhermal emf, Hall coefficiente of electrical resistivity ductivity of zirconium monde. The zirconium carbide sebon at 1800°C in vacuo falls, and lattice parameters for it was found that free electrical resistivity, the line and the thermal conductions.	operty, solid physical protection, absolute thermal emf, Hadacarbide was studied for 36 amples were prepared by full owed by sintering at 2200° or various zirconium samples thermal emf, and the Halles thermal emf, and the Halles	perty,  all coef- 1-48 atom % asing high bec. The les are lers within l coeffi-
Card 1/2		UDC: 546.831'261:	541.12.03



Abs Jour. Refered Enco-Fight. 197, 3 - 75

Author: Tolatoy, M.A., Holomiyett, E.T., Pillowe, M.I., Harring H.T.,

That : Hot Given

Fitle : Photocombection and Loadmond of Fight would be \$5,000

Orig Pub: Ch. elegation of polynomial in a first and fidelity.

5 x 10<sup>-10</sup> g/g). The applicant with the body control of the fit in the startionary photocombect by the transfer of the exciting light of fits. However, and the fitting of the exciting light of the Hotocombect of the exciting and produced the Hotocombect of the Hotoco

Abs Jour: Referst Zour-Fielba, 1917, No. 1, 1919

minisher rapidly. All professionable Laboration in the rest in the red and infrared regions of the process in two minishes. On E. In right concentration of the Parishes with the professional low concentration operations for the Higher Continuous Professional fall of the photocollections Lydge of and the major of the velocity of rice in photocollections Lydge of and the major when the light is twomed on the factor of the call for the minishes incidence when it is twomed on the decrease of the call for my disconcentration operations of the Lydge of the different part of the call of the part of the p

36-68-10/18

AUTHOR:

Krasil'shchikov, L.B., Golikova, O.I., and Novosel'tsev,

Ye. P.

TITLE:

Photoelectric Measurements of Relative Spectral Coefficients

of Brightness (Fotoelektricheskiye izmereniya spektral'-

nykh otnositel nykh koeffitsiyentov yarkosti)

PERIODICAL: Trudy Glavnoy geofizicheskoy observatorii

1957, Nr 68, pp. 152-163 (USSR)

ABSTRACT:

Photographic spectrometry is gradually being replaced by photoelectric spectrometry. The article discusses results of determining the brightness coefficient of brick, slate, and various paints and describes a number of photoelectric apparatus used for this purpose. The article mentions Ye. L. Krinov. There are 14 diagrams and 4 tables, two of

them in the appendix. Of 13 references, 10 are USSR.

AVAILABLE: Library of Congress

Card 1/1

B-5

USSR/ Physical Chemistry - Crystals

GCL TMC24

Abs Jour · Referat Zhur - Khimiya, No 4, 1957, 11000

Author : Tolstoy N.A Kolomiyets B.T., Golikova O.I., Tsentner M.Ya.

Title : Photoconductivity and Luminescence of Polycrystalline CdS(Cu)

Orig Pub : Zh. eksperim i teor fiziki, 1956, 30, No 3, 575-576

Abstract : In the case of polycrystalline samples of CdS-Cu  $(10^{-6} - 5.10^{-4} \text{ g/g})$ were investigated dependence of stationary photoconductivities and luminosi-

ty of glow on intensity of exciting light E (Hg-lines 365, 546 and 578 m ), and also the ratios of surface areas below the curves of photoconductivity rise and drop, and below the curves of increase and attenuation of the glow. The conclusion is reached that results are conflicting with any recombination scheme of the glow and are in accord with the theory of a 2-step mechanism of excitation (Loshkarev V.Ye., Fedorus G.A., Izv.

AN SSSR, Saj. fiz., 1952, 16 81; RZhKhim, 1956, 64335).

Card 1/1

GOL KINA 50-2-22/22 Gayevskaya, G. N. Conference of Young Experts of the Mada Gustayatonl AUTHOR: (Konferentsiya molodykh spetsialistov Glavnov geofizicheskoy Observatory imeni A. I. Voyeykov TITLE: observatorii im. A. I. Voyeykova) Meteorologiya i Gidrologiya, 1958, Nr 2, pp. 61-61 (USSR) PERIODICAL: This conference took place from October 28th - 29th, 1957; assistants of the Leningrad University, of the Arctic Scientific Research Institute, of the All-Soviet Institute ABSTRACT: for Plant Breeding and others took part in it. Lectures were held by young scientists of the conference. A. S. Grigor'yeva's lecture on "the Horizontal Synchronizing Pulse in the Atmosphere" dealt with the computation of the atmospheric coefficient on various isobar surfaces with re-L. P. Spirina's lecture dealt with the forecasts of the ference to the air current. monthly temperature anomalies with reference to the inertia laws. N. A. Timofeyev reported on the calculations of show melting. On the strength of the known laws by Prandtl and of the stage law by D. L. Laykhtman, a formula for the Card 1/3 Car -orated by .oungetion between wetter approximated solution of the - Radiation". ent dispersion according to the

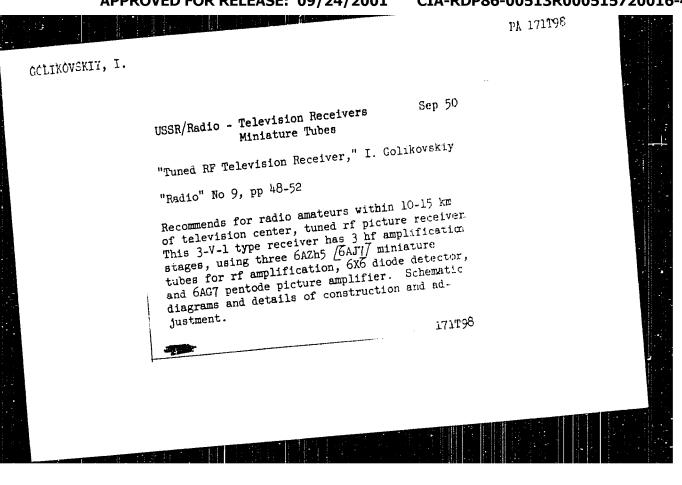
KATARTAN, T.G., glav.red.; SLAGOSLAVOV, 1.F., red.[decensed];
GOLIKOVA, Z.I., red.; GOLOR.IGA, P.Ya., red.; P.G.CZOVA, G.S.,
red.; HILOV, V.I., red.; GEREFERRO, K.S., red.; FALAMARCHUK,
G.D., red.; FOFOV, K.S., red.; SKYGORTSOV, A.F., red.;
ROLIOSHARKAYA, V.A., red.; All OROVA, N.M., tekhn. red.

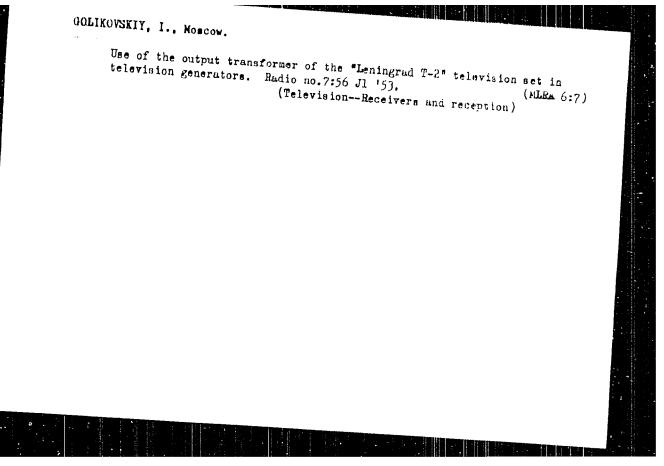
[Problems of viticulture and time making; abstracts for work
for 1696, 1966] Veproxy timegradatativa i vinodallin; abstrakt
referatev nauelmyth rated na 1959-1960 gody. Toukra, Sel'ther1964; 162. 365 p.
(MTRA 15:7)

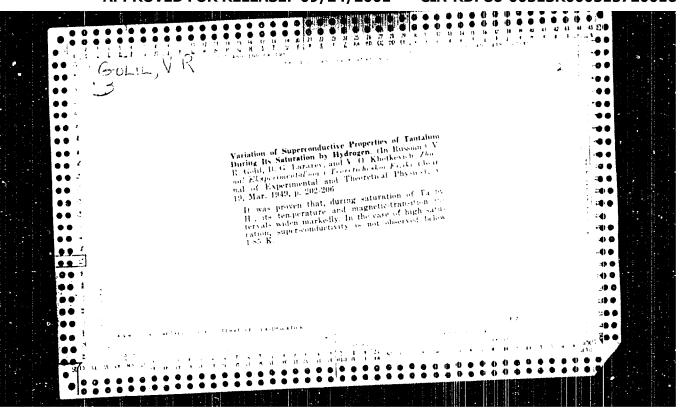
1. Yalte. Veccountry matchno-decisate stel'chi; institut vinodeliya i vinogradatatva "Engarach."
(Viticulture) (Wine and time making)

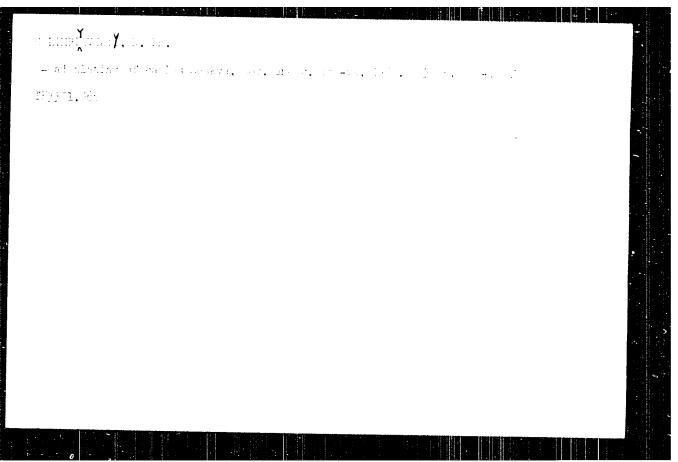
## "APPROVED FOR RELEASE: 09/24/2001

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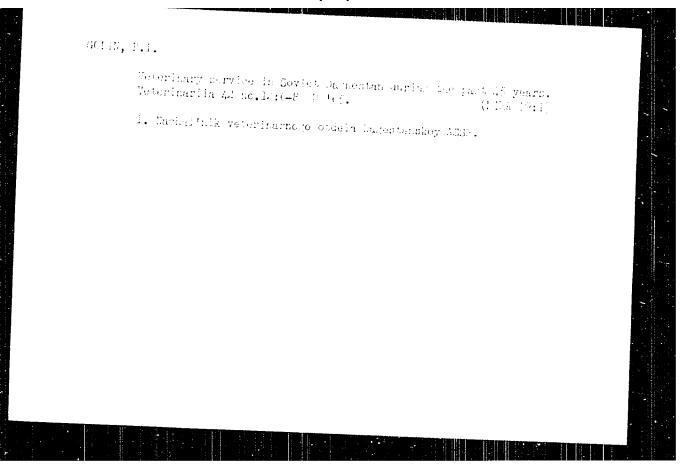
GOLIFFYENERLY, N. Mr.

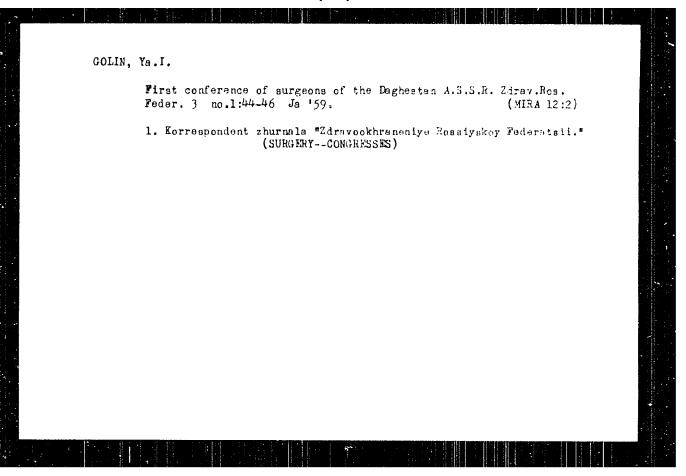
USSE/Electricity - Literature Jun 53
Cables

"Review of N.Kh Golimbiveveking and L.1 Matheret's
Book 'Osvintsevaniye Kabeley' (lead Sheathing of
Cables)" (Engrs D.1. Sharfs, f.M. Laurrik, reviewers)

Elektrichestvo, No 6, p 96

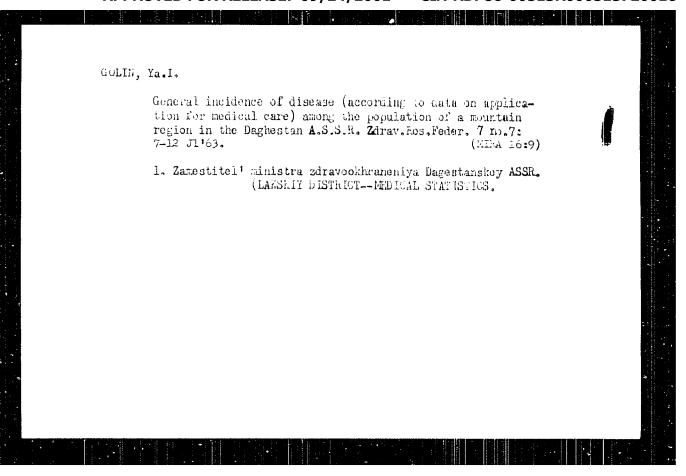
Reviewer calls Golimbiyevsking's and Macheret's
book (136 pp. Gosenergolidat, 1950) a macheneeded
book for technology of cable production, but notes
defects, including insufficient coverage of
lead sheathing of communications and subservinsulated cables and lack of attention to accommy of
electricity of communications and subservinsulated cables and lack of attention to accommy of





Third plenum of the Daghestan Province Committee of the Medical Trade Union. Zdrav.Ros.Feder. 3 no.1:46 Ja '59. (MIRA 12:2)

1. Korrespondent zhurnela "Zdravookhraneniye Rossiys'cey Pederataii." (DAGHESTAH--MEDICAL PERSONNEL)



DZHAVADOV, A.A.; GOLDBA, I.N.

Oll recovery from water-free and watered oil wells in the Sub-Kirmaki series of the Khorasany and Ramany areas in fields of the Oil Field Administration of the Lenin Petroleum Trust. Azerb. neft. khoz. 40 no.1:28-30 Ja '61.

(MIFA 14:8)

(Oil reservoir engineering)

12 17

\$/070/61/006/003/009/009 E073**/E**535

24.7800(1153,1160,1136)

Golina, Yu.I., Kashtanova, A.M., Maksimova, G.V. and

Skanavi, G.1. (Deceased)

TITLE: Producing single crystals of strontium-titanate and

some data on their dielectric properties

PERIODICAL: Kristallografiya, 1961, Vol.6, No.3, pp. 473-475

TEXT: In other work the authors deal with the results of tests on growing single crystals of SrTiO, by the method of Verneuil from a charge produced by sintering equimolar parts of TiO, (r) and SrCO,. The obtained single crystals were dark-brown, tg & equalled 0.007 to 0.0006, Laue patterns taken after annealing for 24 hours at t = 1200°C with subsequent slow cooling indicate the presence of tension and twining. More perfect crystals were grown from charges produced by the oxalate method. In this paper the method of preparing such charges and some data on the electric properties of the produced single crystals are given. The preparation of SrTiO, from strontlum oxalate and titanate was as follows. The saturated solution of distilled TiCO, which compared by gradual addition of the latter to water. It was experimentally

Card 1/6

AUTHORS:

:27.

Producing single crystals of ... \$/070/61/006/603/069/069 E073/E533

established that saturation was reached whenabout 40 ml TiCl $_4$  was added to 100 ml of water. The concentration of the obtained solution was determined by precipitating titanium with assemble and subsequent weithing in the form of  ${\rm TiO}_2$ . Then, a 25% solution of SrCl, was prepared and both solutions were mixed, the obtained cold mixture was poured into a prepared 10% solution of hot ammonium oxalate. For neutralizing the forming oxide, ammonic was added until a smell could be detected. The obtained precipitate of a double salt of Sr and Ti oxalate was washed in water to remove chlorine, dried and sintered at  $450\,^{\rm o}{\rm C}$  for one hour so as to obtain SrTiO<sub>3</sub>. After sintering, the powder was coushed in a porcelain mortar to such a size that it should pass through a sieve with 1000 holes per cm<sup>2</sup>. Single crystals of SrTiO<sub>3</sub> were grown according 1000 holes per cm $^2$ . Single crystals of SrTiO $_3$  were grown according to the Verneuil method in a corundul furnace. SrTiO $_3$  for as with silit rods, which are used as supports, easily fusible compounds, as a result of which the base of the crystal becomes soft. To prevent this, the base of the cone of the charge shoul! be located in a zone with sufficiently low temperatures. It was established experimentally that the lase of the cone should be at a distance of 3 cm from the top at the instant of formation of a Card 2/6

3.27.28

Producing single crystals of ...

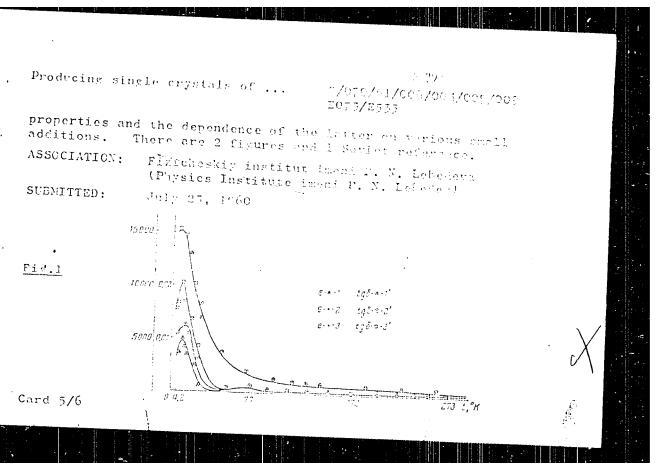
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drop on it (t $\simeq$  2000°C), therefore, prior to drop formation, the charge cone was 3 cm high. In a number of experiments bases were used which were made of pressed SrTiO3 powder sintered at 1400°C. The crystals were grown without germinations at an average speed of 10 to 30 mm/hour. The flame conditions varied from a reducing one to an oxiding one. Under oxiding conditions, bright transparent crystals 30 mm long with a diameter of over 5 mm were produced. The reflection index determined by the immersion method equalled 2.39. According to spectrum analysis, the contents of the admixtures did not exceed the following values in  $\%: Mg \rightarrow 0.006$ , Si  $\rightarrow 0.006$ , Al  $\rightarrow 0.01$ , The produced single crystals were annealed to remove Fe = 0.003internal stresses. Then, slices 6 x 5 x 1 mm were cut perpendicularly to the axis of growth. Silver electrodes were burned on after the coherence of the surface had been checked by a microscope. The dielectric constant varied between 315 and 320 and was independent of frequency. At somic frequencies tg o did not exceed 0.004. Fig.1 shows the dependence of  $\epsilon$  and tg  $\delta$  on the temperature for  $SrTiO_{\frac{1}{2}}$  single crystals at the frequencies 200 c.p.s., 1 and 5 kc/s for the values denoted by 1, 2, 3 and 1, 2', 3' in Card 3/6

Producing single crystals of

\$/070/61/006/003/009/009 E073/E535

At temperatures below  $77^{\,9}\mathrm{K}$  a sharp increase in  $\epsilon$  was In the range 3 to 4°C above the liquid helium temperaobserved. ture  $\epsilon$  remains practically constant, reaching a value of about 15 000. The temperature dependence of tg o is characterized by a very pronounced maximum (at T  $\sim$  13 K), the position of which is practically independent of frequency In the temperature range 48 to 98 K a second, weak maximum was observed for tg  $\delta$ , which shifts towards higher temperatures with increasing frequency. Investigation of the dielectric hysteresis was at 295, 77, 4,2 °K. No hysteresis loops were detected at room temperature and liquid nitrogen temperature. The maximum potential of the electric field in these cases did not exceed 30 kV/cm. The results obtained at liquid helium temperature are plotted in Fig.2 (graph 1 - E = 1 kV/cm, graph 2 - E = 3 kV/cm, graph 3 - E = 5 kV/cm. They show that, at this temperature, the hysteresis loop is very narrow without a pronounced saturation. Due to breakdown of the investigated specimens, the authors were unable to observe hysteresis loops at higher field strengths. Work is proceeding on elucidating the influence of the purity of single crystals on their dielectric Card 4/6

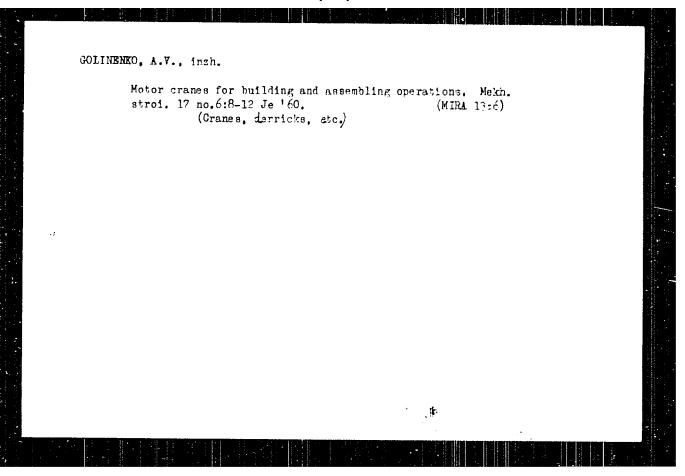


50732-65 EWT(m) Pe CCESSION NR: AP5016339	DIAAP	<b>P</b> 0/0046,	/65/01.0/1 <b>3</b> 0	2/0123/0130	75"   12	
UTHOR: Radwan, Maciej (Ra Jerzy (Stanyuk, G. ); Krzy	dvan, M.); Golince siak, Barbara (Kar	ok, Henryk (G	ilin'olak,	G.): Stasiuk		
ITLE: Indirect method det	ermining the conte	mination of g	cound with	foll-out		
OURCE: Nukleonika, v. 10,	no. 2, 1965, 123	130				
OPIC TAGS: stronium, isot	ope, radioactive (	contemination,	radioseti	ve fellout		
BSTRACT: The concentration laces and several years were prepared from ash. The ured by use of several components of the concentration by fallout. Orig. articles	as investigated. I e activity of thos unters. It was for e. This can be tal	Pleces of born se specimens ( and that the c ien as a crite	were bur iry sad li moent ati	ned (nd sampl quid) was mea on of stronti	es T	
SSOCIATION: Wojskowa Akad	emia Tebbnicana, V	Jarsaw (Milita				
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GOLINENKO, A.V., inshener.

Increase the efficiency of excavator machinery. Gor.khoz.Mosk. 25 no.10:35-(Millà 6:11)

(Excavating machinery)



KAMENSKIY, M.D.; GOLINETS, M.V., redaktor; ZABRODINA, A.A., tekhnicheskiy redaktor.

[Electric systems] Elektricheskie sistemy. Izd. 2-oe, perer. 1
dop. Leningrad, Gos. energeticheskoe izd-vo, 1952. 248 p.[Photostat]
(Electric networks)

(MLRA 8:2)

AUTHOR:

Golinets, M. V., Engineer

JUTY 155-56-7-26/32

TITLE:

All Union Scientific-Tachnical Conference on the Electrification of Towns and Rural Districts of the USSE (Vsesoyutnoye nauchno-tekhnisheskeye soveshehaniye po elektrificatsii parodov i

ragonov SSSR)

PERIODICAL:

Elektrichectvo, 1998, Nr 7, pr. to + po ("COR)

ABSTRACT:

The conference was convened in May, 1950, by the Central Board of Directors of the NTOEP together with the Institute of Power Engineering AS USSR in Leningrad. 424 gamens from loo cities attended the conference. Furthermore representatives of 60 Sovnarkhones, of the Ministry of Electric Power Stations, of the State Scientific-Technical Committee Attacked to the Council of Ministers of the USSR and to the Councils of Mini ters of the Union Republics (Gooddarstvennyy nauchoa-technich whiy kositet Soveta Ministrov SSSR) of the googlans of the union- and autonomous regulies, of the planning- and scientific research institutes. To reports were delivered at a Syrongataihov (State Scientific-Technical Committee Att and to the Council of Ministers

Card 1/4

of the USCR) upoke about the "Fundemental Trailed of the Electri-

All Union Scientific-Technical Conference on the 307, 155-58-7-26/32 Electrification of Towns and Rural Districts of the USS:

fication of the Country". S.R. Kachehenko (Teploelektroproyekt) rejusted on the results of the work carried out by the Teploelektroproyekt on the basis of the scheme for the levelopment of the power engineering of the USSR till 1970. D.G. Kotilevskiy (Ministry of Electric Power Plants USSR) reported on the functions of the ministry at the time after the reorganisation of the industrial administration. Ya.M. Chervenenkis (Gigrokommunenergo) reported on the electric supply of towns and of workmen's colonies of the RSFSR, Ye.O. Shteynganz, Moscow Engineering Economics Institute (Moskovskiy inshenerno-ekonomicheskiy institut) dealt with coveral problems concerning the planning of the electric supply of the cities, G.V. Sheremet'yev (Gijrosol'elektro) reported on the basic scheme for the electric energy supply of agriculture in the USSR during the coming to - 15 years which had been worked out from 1954 to 1955 in the Giprosel'electro ani defined precise ly in 1957. S.M.Roshkov (Institute of Power Engineering AS USSR) dealt with the electric supply of agricultural consumers by means of the electric-supply lines of e.c. powered railway, S.D. Volobrinskiy, Leningrad Institute of Railway Engineers (Leningradskiy institut inchenerov chelecnodorozhnogo transporta)reported on

Card 2/4

All Union Scientific-Technical Conference on the 307/05-58-7-26/72 Electrification of Tours and Rural Districts of the USSR

the possibility of taking energy is ediately from the electric--supply line of railways powered with a.c. of injustrial frequency, V.M.Mikhaylova, Leningrad Jolytechnical Institute (Leningradskiy politekhnicheskiy institut) reported on the analysis of the technical-economic parameters in the electric supply of remote regions on the basis of tap lines from the electric supply network. Yu. Ya. Mazur, Institute of Fower Engineering, Latvia SSR (Institut energetiki i elektroniki Latviyskoy SSR) dealt with problems which result from the operation of small power plants in energy systems. The discussions were attended by: I.A. Nikulin (Sovnarkhoz, Krasnoyarsk), 4.7. Komerov (Sovnarkhoz, Tatar ASSR), M.D. Jornshteyn (Sovnarkhon, Novocibirsk), A.M. Surkisyan (Jlave 11electro), J.D. Polykovskiy (Sovnarkhon Leningrad), G.V. Smirnov (Ministry of Electric Power St. tions USSA), M.D. Kamenskiy (Leningrad Polytechnical Institute), G.V. Vonyatytskiy (Gosplan Latvia SSR), Yu.K.Stolyarov (Sovnarkhon, Stalingead), G.C.Levit (Central Administration of the NTORF), V.V. replantant (Sovnarkhon, Lithrania) and others, altogether 32 persons.

Card 3/4

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All Union Scientific-Technical Conference on the 307/105-58-7-26/32 Electrification of Towns and Rural Districts of the USER	
L. Electria power production483R I. Conferences	
Card 4/4	

BASOV, A.N.; GOLINEV, M.P.; GUTTSAYT, Z.I.; PAZHITNOV, V.N.

Classification of crude oils according to qulaity and the differentiation of their prices. Khim.i tekh.topl. i masel 7 no.11:45-50 N 162.

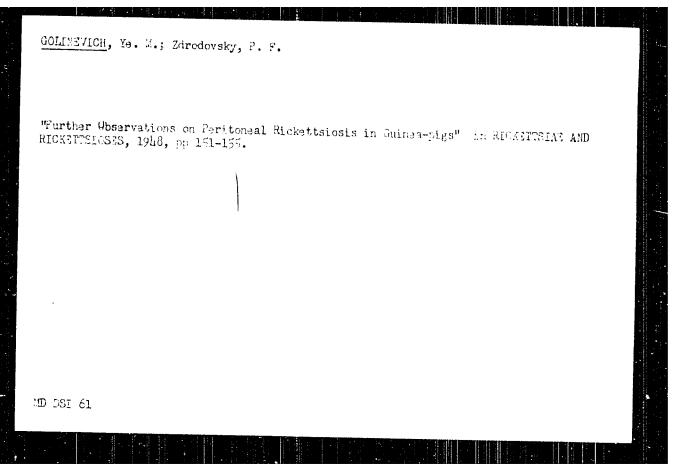
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1. Vsesoyuznyy nauchno-issledovatel'skiy institut po pererabotke nefti i gazov i polucheniyu iskusstvennogo zhidkogo topliva. (Petroleum-Prices)

GOLINEVICH, Ya. M., Edredovsky, P. F.

"Experimental Analysis of the Action of Antimeningococcus Serum"

SOURCE: Arkhiv Biol. "auk, Ser. Biol, 193h (2)



"Immunity to Typins infection," in RICKITSIAN ARCHITSIANS, 17h8, pc 12h-199

MD DOI 61

GOLINIVICH, Ye. M.; Zdrodovsky, P. F.

"Experimental Observations on Marseilles Faver," in RIGHSTISIAS AND RIGHSTISIASS, 1940, pp 216-244.

MD DSI 61

GOLIVEY(ICH, M. M.

"Sur le système de rickettsioses a tiques"

Journal Microbiol, Spidemiol et Immunol, No 10, pp 23-35, 1949

GOLINEVICH YOU K

The Committee on Stelin Prizes (of the Council of Ministers USSR) in the fields of science and inventions amnounces that the following scientific works, popular scientific books, and textbooks have been submitted for competition for Stelin Prizes (or the years 1952 and 1953. (Sovetakaya Kultura, Moscow, No. 22-No. 20 Peb - 3 Apr 1956)

Raud

Title of Work

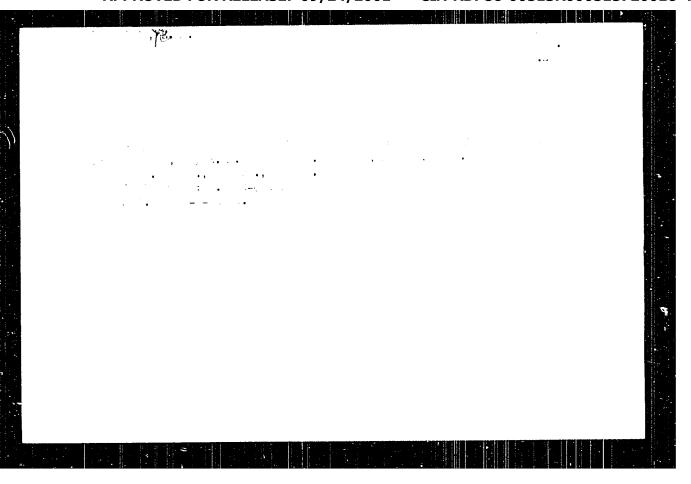
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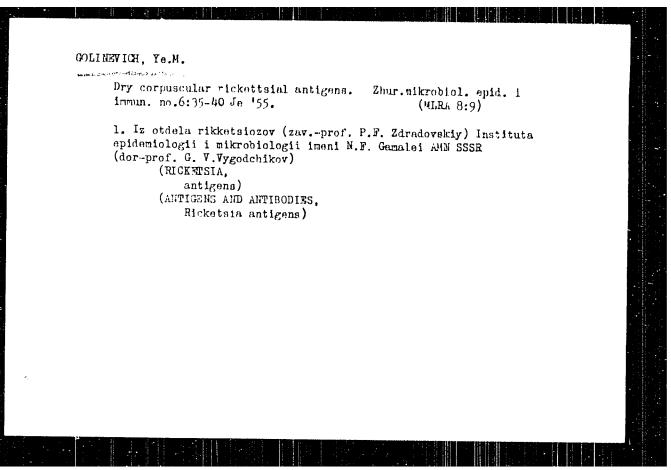
Golinevich, Ye. M.

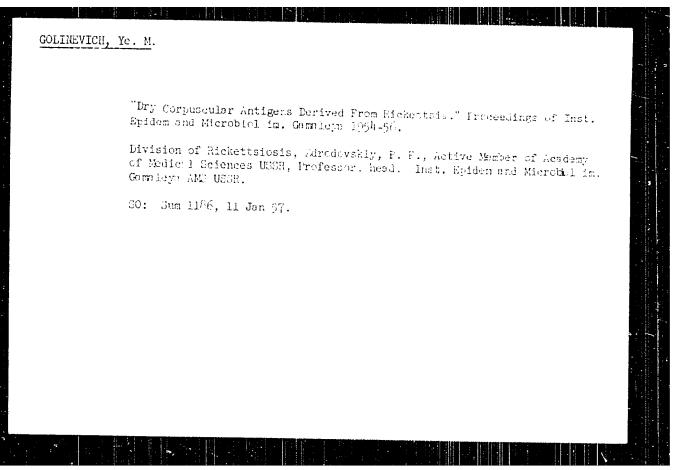
"Teaching on Rickettsine and Ricketsioses"

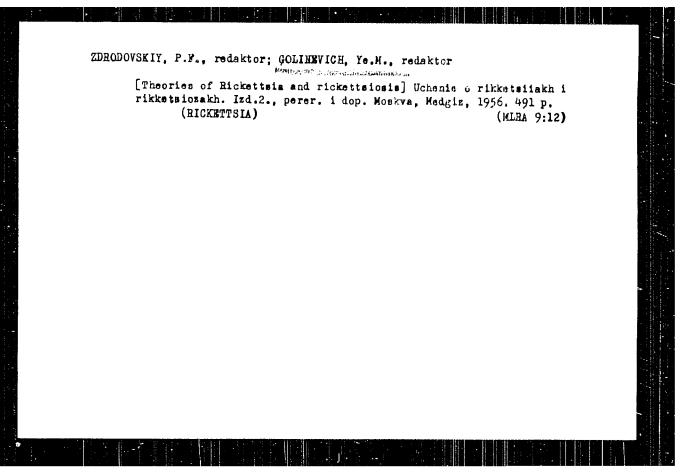
Institute of Epidemiology and Microbiology imeni N. G. Gamaley, Academy of Medical Sciences USSR

SO: W-30604, 7 July 1954









ZDRODOVSKIY, P.F., GOLINEVICH, Ye.M. YABLONSKAYA, V.A.

Characterization of the Z strain of Rickettaic promatchi and its mathegenic properties [with summary in English]. Von.virus. 3 no.9:136-142 My-Je '58 (MIRA 11:7)

1. Otdel rikketsiczov Institute epidemiologii i nikrabiologii imeni N.F. Gamalei ANN SSSR, Moskva.

(RICKETES LA, PROMAZEKII.

characterization & mathegen. properties of new strain.

(Rus))

Differentiation of organisms causing Kenya tick typhus and Indian tick typhus.[with sugmary in English]. Voc.virus 3 no.41202-206 J1-Ag '58 (MRA 11:9)

1. Otdel rikketsiczov Instituta eridemialagii i mikrabiologii imeni N.F. Gamalei AMI SSSR, Moskva.

(RICEPTISIA.

differentiation of atraina causing Kenya tick typhus causing Indian tick typhus (Mus))

ZDRODOVSKIY, P.F., SOLIMEVICH, Ye.M.

Immunoperio propertic of Middlettain proceeded; strain E. [with customy in English]. Vop.virus 3 no.61266-165 S-0 168 (M.E.: 18120)

1. Otdel mikhetsissov Instituta opeidniologii i mikrobiologii imeni N.F. Gameleya AMN SSSR, Moskov.

(RICKELIST: PRO AMERIC.

B. immunografe properties (Rue))

GOLINEVISH, Ye.M.; GERIC, V.A.

Associated immunization against typhus fever, Q fever, and tick-boome rickettslosis in northern Asia in experiments on guinea plgs. Vop. virus. 6 no.5:598-602 S-0 '61.

1. Otdel rikketslozov AMN SSSM, Moskva. (VACCINALION)

(MICKETTSIAL DISCASES)

(VACCINALION)

GOLINEVICH, Ye.M.; GEHIG, V.A.

Associated vaccine against exacthemamatous tophus and 2 fever and the possibility of decreased reactogenic properties of the vaccine against 2 fever. Vop. virus. 6 no.6:728-732 N-D \*61. (Min. 15:2)

1. Institut epidemiologii i mikrobiologii imeni N.F.Gamalei AMN 385.k. (2 FEVER) (TYPHUS FEVER.) (VACCINGS)

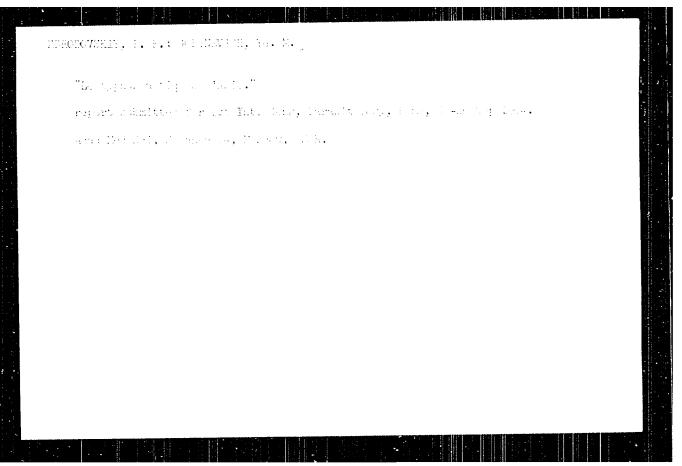
ABELEV, G.I., kand. med. nauk; BUFRINSKAYA, A.G., kand. med. nauk; GEL'TSER, R.R., prof.; GGLINEVICH, Ye.M., prof.; ZHDANCV, V.M., prof.; ZDRODOVSKIY, P.F., prof.; KALINA, G.P., prof.; KAULEN, D.R., kand. med. nauk; KIKTENKO, V.S., prof.; KRYLOVA, O.P., kand. med. nauk; KUGHERENKO, V.D., kand. med. nauk; LOMAKIN, M.S., kand. med. nauk; MOSING, G.S., doktor med. nauk; PERSHINA, Z.G., kand. sel'khoz. nauk; PEKHOV, A.P., doktor biol. nauk; PESHKOV, M.A., prof.; TIKHONENKO, T.I., kand. med. nauk; TOVARNITSKIY, V.I., prof.; SHEN, R.M., prof.; ETINGOF, R.N., kand. med. nauk; KALININA, G.P., prof., nauchnyy red. toma; ZHUKOV-VEREZHNIKOV, N.N., prof., otv. red.; VYGODCHIKOV, G.V., prof., zamest. otv. red.; TIMAKOV, V.D., prof., zan. otv. red. BAROYAN, O.A., prof., red.; KALINA, G.P., red.; PETROVA, N.K., tekhn. red.

[Multivolume manual on the microbiology, clinic, and epidemiology of infectious diseases]Mnogotomnoe rukovodstvo po mikrobiologii klinike i epidemiologii infektsionnykh boleznei. Moskva, Medgiz, Vol.2. [General microbiology]Obshchaia mikrobiologiia, Red. V.M. Zhdanov. 1962. 535 p. (Continued on next card)

COLITEVICH, E.M. [Colinevich, Ye.M.] TABLGISKAYA, V.A.

Live typhus vaccine prepared from strain "E" of Rickettsia prowazeki. J. Hyg. epidem. 7 no.3:290-300 '63.

1. Gamaleya Institute od Epidemiology and Microbiology, Academy of Medical Sciences of the ".S.S.R., Rickettsiae Department, Moscow.



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ACCESSION NH: AP4022936 S/0248/64/000/003/0049/0058

AUTHOR: Golinovich, Yo. M.; Fryazinova, I. B.

TITLE: Antigenic and immunogenic fractions of "whole" antigens from richettaial cultures grown in chicken embryos

SOURCE: ANN SSSR. Vostnik, no. 3, 1964, 49-58

TOPIC TAGS: rickettsial disease, tick-borne fever, typhus, "whole" antigen, antigen fraction, R. prowazeki, R. mooseri, D. sibericus, armonium sulfate precipitation, complement fixing reaction, typhus vaccine, immunogenic property, allergenic property

ABSTRACT: Rickettsial "whole" antigons of typhus and tick-borne spotted fever grown in chicken embryos have been successfully used in direct and differential serodiagnosis. They have been found equal to corpuscular antigens in quality, easier to prepare, and to contain highly immunogenic properties. However, they cannot be recommended as a vaccine because of the considerable admixture of egg protein. In the present study the antigen fractions were isolated from "whole" antigens (R. provazeki, R. mooseri, and D. sibericus) by pracipitation with varying amounts (15 to 35%) of ammonia sulfate and the antigenic,

ACCESSION NR: AP4022936

immunogenic, and allergenic properties of the lysate prote n fractions and "whole" antigens were compared. Antigen activity was determined by complement fixing reaction. Immunogenic properties were determined by reactions of immunized guinea pigs to virulent culture "noculations" a month after immunization. Allergenic properties were based on skin reactions of guinea pigs to subcutaneous injections. Findings show that R. prowazeki "whole" antigens (5.58 mg/ml protein or 798 micrograms/ml nitrogen) precipitated with 25% ammonium sulfate produces the purest antigen fraction with minimum quantities of protein (0.338 mg/ml or 22 micrograms/ml nitrogen) and can be recormended as a typhus vaccine. Antigen fractions of R. prowazeki and D. sibericus "whole" antigens produced by precipitation with 25 and 35% ammonium sulfate cause specific allergic reactions and can be used as allergens. Orig. art. has: 9 tables.

ASSOCIATION: Institut epidemiologii i mikrobiologii im. N. F. Gamalei, Moscow (Epidemiology and Microbiology Institute)

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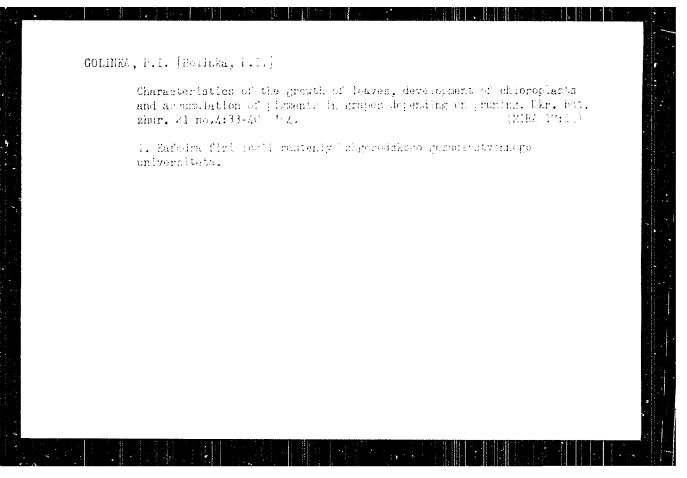
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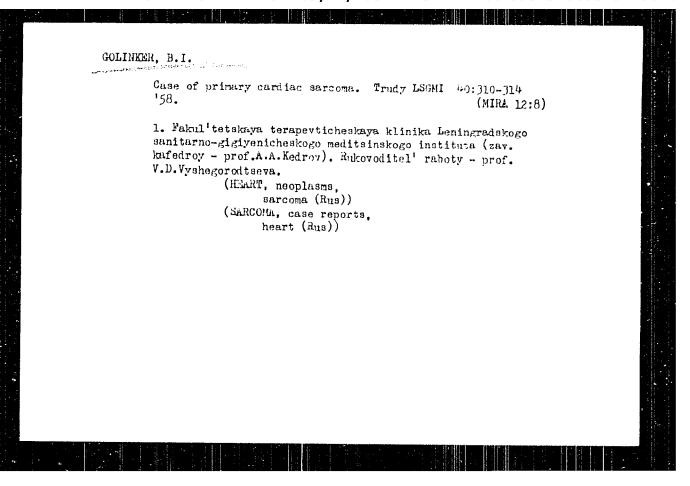
1. Ostrodek Instytutu Techniki Budowlanej, Krakow.

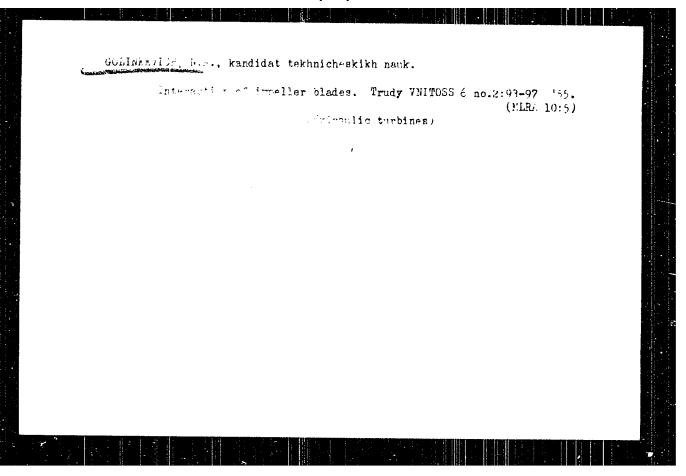
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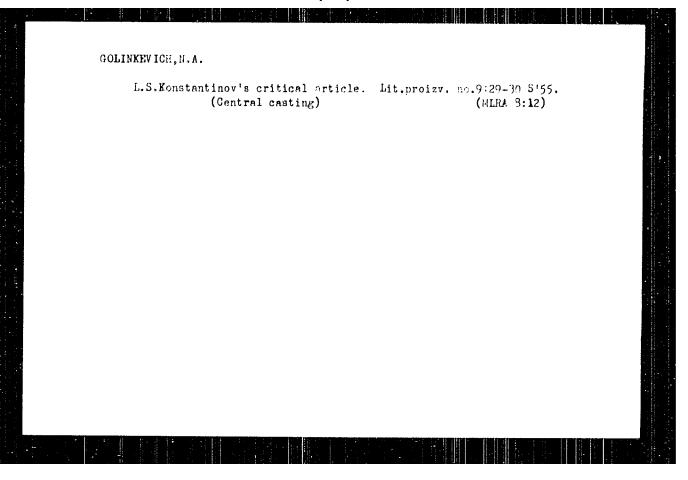
Dynamics of pigment accumulation in graps leaves during the vogetation period, The. bot. zhur. 20 no.4:40-44 163; (MIRA 1712)

1. Unhygrodskip goradarstvanayy universitet. Rafedra fiziologii rasteniy.









125-1-1184

Translation from: Referativnyy Zhurnal, Mashinostroyeniye, 1957,

Nr 1, p. 174 (USSR)

AUTHOR:

(306 12 40 V

Golinkevich, N.A.

TITLE:

How to Increase the Effectiveness of Guide Nozzles of Screw Propeller When Reversing (O povyshenii effektivnosti napravlyayushchikh nasadok k grebnym vintam

pri rabote na zadniy khod)

PERIODICAL: Tr. Gor'kovsk. politekhn. in-ta, 1956, 11, Nr 4,

pp.33-52

ABSTRACT:

On the basis of results obtained from tests conducted at the Gor'kiy Polytechnic Institute with several patterns of nozzles, the author attempts to explain the causes of a sharp decrease in the thrust of the propulsion unit,

Card 1/2

SOV /124-58-5-5410

Translation from Referativnyy zhurman, Mekhanika, 1958, Nr. 5, p.54 (USSR)

AU THOR

Golinkeyich, N. A.

TITLE

Or One of the Possible Modifications of Impeller-vane-type Propalsors (Ob odnov iz vozmozhnykh modifikatsiv kryl'-

chatogo dvizhitelya)

PERIODICAL Tr. Gor'kovsk, politekhn, in-ta, 1956, Vol 12, Nr 3, pp 5-9

ABSTRACT

To reduce nonuniformity in the azimuthal (cyclic) loading of the impeller vanes of vane-type propulsion mechanisms, the author proposes varying the angle of pitch of the impeller blades.

G.I. Maykapar

1. Engled terms—Design

Card 1/1

GOLINKEVICH, N.A., kand.tekhn.nauk

Effect of slot flow on the degree of circulation velocity along the propeller blade profile in the nozzle. Trudy GPI 14 no.1:
34-37 158.
(Propellers) (Hydrodynamics)

(Propellers) (Hydrodynamics)

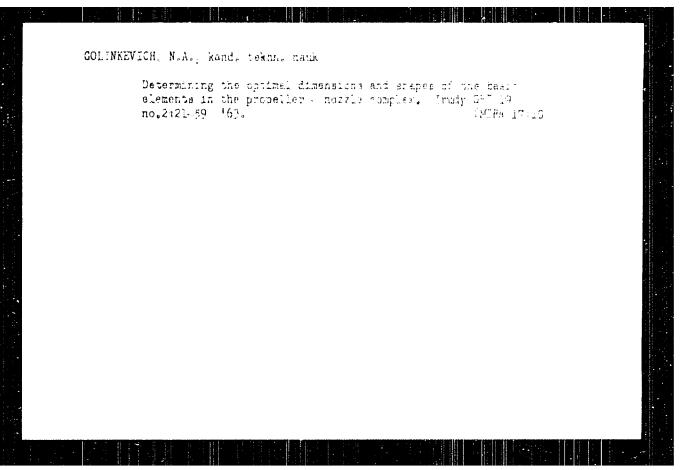
AHRAMOV, V.V., kand.tekhn.nauk; AGEYEV, D.V., doktor tekhn.nauk; prof.;

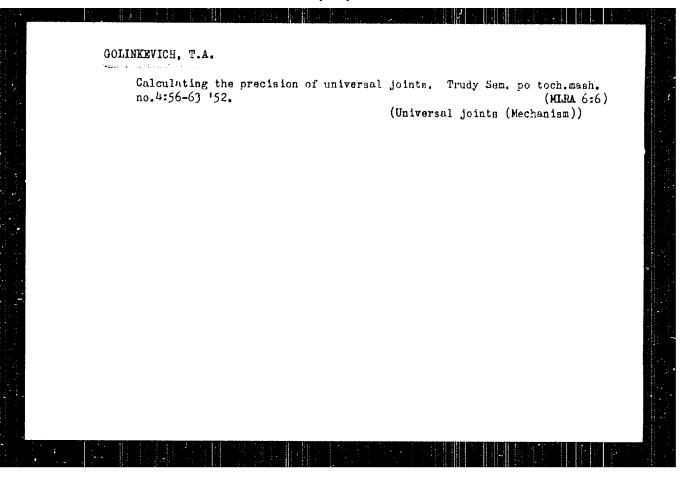
RAMDAS, A.M., doktor tekhn.nauk, prof.; VARMOVSKIY, A.V., doktor
tekhn.nauk, prof.; GOLHKEVICH, W.A., kand.tekhn.nauk, dotn.;
DERTEV, M.K., doktor.tekhn.nauk, prof.; MATTES, M.V., doktor tekhn.
nauk, prof.; RYZHIKOV, A.A., doktor tekhn.nauk, prof.; PASYMKOV,
O.N., otv.za vypusk

[New method for calculating thermal stresses] Bovyi raschetnyi
metod vychialeniia termicheskikh napriazhenii. Gor'kii, 1958.
57 p. (Gorkiy.Politekhnicheskii institut. Trudy, vol.14, no.3)

(MIRA 13:7)

(Thermal stresses)





GOLINKEVICH, LA

PHASE X TREASURE ISLAND BIBLIOGRAPHICAL REPORT AID 539 - X
[Supercedes AID 539-1]

FOOK Call No.: AF639799

Author: GOLINKEVICH, T. A. and DORONIN, I. L. Full Title: BASIC PRINCIPLES IN DESIGN AND MANUFACTURING OF INSTRUMENTS Transliterated Title: Osnovy proyektirovaniya konstruktsiy i

tekhnologicheskikh protsessov v priborostroyenii

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The authors express thanks for valuable assistance to the following Shatalov, A. S., Doc. of Tech. Sci., Prof., Karpov, L. I., Kand. of Tech. Sci., Dotsent, Kashepava, M. Ya., Kand. of Tech. Sci., Dotsent PURPOSE AND EVALUATION: This is a textbook authorized by the Ministry of the Defense Industry, USSR for students of technical colleges. It may also be useful to workers of the instrument manufacturing industry. It is an elementary textbook on planning mechanical layouts for instrument design. The author is mainly concerned with kinetics. Basic problems of special instrument design are considered on the example of

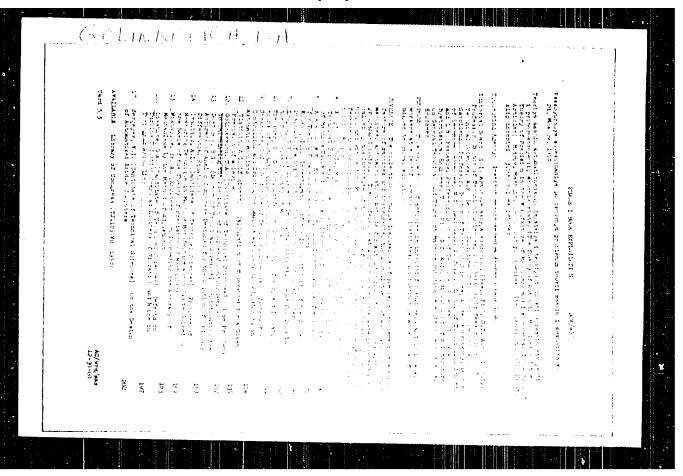
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	GOLINKEVICH, T. A.	•
	T. A. Golinkevich, "On the Calculation of Accuracy of Complicated Calculators."	
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Golinkevich, T.A.

AUTHOR:

Some problems in calculating the accuracy of complex

computers

PERIODICAL

Referativnyy zhurnal. Avtomatika i radloelektronika, no. 4, 1961, 10, abstract 4 B65 (V sb. feoriya mashin avtomat, deystviya i teoriya tochnosti v mashinostr. i priborostr., M., Mashgiz, 1960, 152-157)

TEXT: The following topics are of importance in calculating the accuracy of complex computers: 1) The sequence of calculations. The setting-up of equations should be performed in accordance with the programming system of the computer and in the direction from the output towards input. 2) The primary errors should be defined as follows: a) non-random errors by definite numerical quantities and relations; b) random quantities by mean value and dispersion; and c) random processes by mean value and spectral density. 3) The

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